

Substrate effects on V_2O_3 thin films

Udo Schwingenschlög^{1,2,3*}, Raymond Frésard³, and
Volker Eyert^{3,4}

¹*ICCMP, Universidade de Brasília, 70904-970 Brasília, DF, Brazil*

²*Theoretische Physik II, Institut für Physik, Universität Augsburg, 86135
Augsburg, Germany*

³*Laboratoire CRISMAT, UMR CNRS-ENSICAEN(ISMRA) 6508, and IRMA,
FR3095, 14050 Caen, France*

⁴*Center for Electronic Correlations and Magnetism, Institut für Physik,
Universität Augsburg, 86135 Augsburg, Germany*

Abstract

We apply density functional theory and the augmented spherical wave method to analyze the electronic structure of V_2O_3 in the vicinity of an interface to Al_2O_3 . The interface is modeled by a heterostructure setup of alternating vanadate and aluminate slabs. We focus on the possible modifications of the V_2O_3 electronic states in this geometry, induced by the presence of the aluminate layers. In particular, we find that the tendency of the V $3d$ states to localize is enhanced and may even cause a metal-insulator transition.

Key words: density functional theory, electronic structure, V_2O_3/Al_2O_3
heterostructure

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1 Introduction

V_2O_3 is a classical example of a material which is located in the vicinity of a Mott transition. The latter can be triggered, for example, by Cr-substitution [1] or by the application of external pressure [2]. In this respect depositing thin films of V_2O_3 on a substrate with a slightly smaller in-plane lattice parameter a is likely to provide another way of inducing a Mott insulator-to-metal transition. Indeed, V_2O_3 thin films are nowadays attracting great attention, since they promise further insight into the mechanism of the Mott transition [3,4]. In this context, the observation of a thickness-dependent metal-insulator transition (MIT) in ultrathin films has been attributed to an increasing c/a lattice parameter ratio (decreasing a , increasing c) because of interaction with the Al_2O_3 substrate [5]. In contrast, detailed X-ray diffraction experiments for high quality films indicate a more complex thickness-dependence of the lattice parameters [6]. In particular, they do not point to systematic changes of the c lattice constant for film thicknesses ranging from 100 Å to 1000 Å.

In this Letter, we aim at clarifying the influence of the substrate on the electronic states of V_2O_3 thin films grown on Al_2O_3 . Indeed, for ultrathin films a significant reorganization of the electronic excitations of the film material may be induced by those of the substrate, going beyond geometric effects. In general, the properties of heterointerfaces in many cases deviate considerably from those of the component materials. A prominent example in this context is the quasi two-dimensional electron gas formed at the interface of the insulators $LaAlO_3$ and $SrTiO_3$ [7,8,9]. However, as we will show below, the impact of an Al_2O_3 interface on the near- E_F density of states in V_2O_3 is rather weak

* Corresponding author. E-Mail: schwinud@physik.uni-augsburg.de

as soon as the heterostructure involves several V_2O_3 layers.

To describe the electronic effects, we model the interface as a heterostructure consisting of alternating slabs of the component materials. Comparing the V $3d$ partial densities of states as resulting from the heterostructure calculation to the corresponding bulk data we find only a weak response of the vanadate to the bonding with the aluminate. However, the reduced dispersion of the V $3d$ states perpendicular to the layers leads to a narrowing especially of the a_{1g} bands, which might suppress the intrinsic metallicity of V_2O_3 .

2 Structural and calculational details

The unit cell used for modeling the heterostructure is the canonical threefold hexagonal supercell of the trigonal corundum lattice. It comprises six formula units as well as a stacking of six metal layers along the hexagonal c axis. These layers are separated by layers of O atoms, which form octahedra around the metal atoms. In order to set up the heterostructure, we divide the hexagonal supercell into a V_2O_3 domain and an Al_2O_3 domain, both consisting of three metal layers as well as the corresponding O layers. The c lattice constants and the fractional coordinates of the atoms in the two slabs are those of bulk metallic V_2O_3 [10] and Al_2O_3 [11], respectively. In contrast, since V_2O_3 is grown on an Al_2O_3 substrate, we adopt the a lattice constant of the aluminate for the whole supercell. Because the a lattice constant of bulk V_2O_3 is about 3.5% larger as compared to that of bulk Al_2O_3 , a relevant interface stress is induced, which could modify the V valence states. However, no structural relaxation has been found in the experiments [6]. Since a minor relaxation beyond the experimental resolution does not affect our further conclusions, a

structure optimization consequently is dispensable.

Finally, using periodic boundary conditions we obtain a multilayer structure of alternating V_2O_3 and Al_2O_3 slabs, as illustrated in Fig. 1. The O atoms, which form a sublattice of space-filling octahedra, are omitted in this representation, since they maintain the positions of the parent compounds. For further details of the structural aspects of V_2O_3 and related oxides see Ref. [12] as well as the references given therein. We have checked that our results do not depend on the supercell setup, i.e. the thickness of the supercell in c direction and the thickness of the V_2O_3 slab.

Our investigation is based on density functional theory within the local density approximation. We use a new full-potential version of the augmented spherical

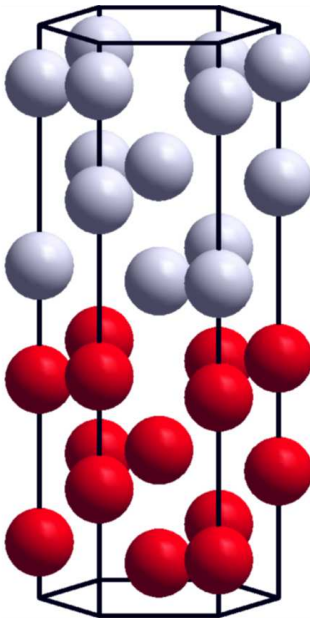


Fig. 1. Hexagonal unit cell of the V_2O_3/Al_2O_3 heterostructure, as used in the calculations. The light gray and red (b/w: dark gray) spheres denote V and Al sites, respectively. The figure shows six buckled (horizontal) planes of V/Al atoms. For clarity, the O atoms have been omitted. They form the well-known O sublattice of corundum V_2O_3 and Al_2O_3 , see the detailed description in Ref. [10].

wave method [13,14]. The basis set contains Al $3s$, $3p$, $3d$, O $2s$, $2p$, and V $4s$, $4p$, $3d$ orbitals and is complemented by states of additional augmentation spheres. Brillouin zone integrations were performed using the linear tetrahedron method on a mesh of up to 264 \mathbf{k} -points within the irreducible wedge of the hexagonal zone.

We point out, that the well-known shortcomings of the local density approximation necessitate a careful analysis of the electronic structure in order to derive reliable conclusions as strong correlation effects are largely ignored in this approach. As has been pointed out by Brinkman and Rice and elaborated by others [15,16,17,18], such correlation effects may affect the metallic behavior especially if narrow bands are present near the Fermi energy. Thus, the following line of reasoning is closely related to previous work on the phase transitions in vanadium and titanium oxides [19,20,21] and influenced by the results of recent LDA+DMFT calculations for bulk V_2O_3 [22,23].

3 Results and discussion

Turning to the results of our calculations, we compare in Fig. 2 the V $3d$ partial densities of states (DOS) of metallic bulk V_2O_3 to those of the heterostructure. For a more detailed discussion of the band structure and DOS of V_2O_3 [21] and related vanadates [12] we refer the reader to the literature. According to Fig. 2, even for a V_2O_3 triple-layer the essential features of the V $3d$ electronic states largely resemble those of bulk V_2O_3 . Besides minor differences of the DOS shape, the energetic positions of the main peaks are very similar. This holds for both the (partially occupied) t_{2g} and the (unoccupied) e_g group of states. Importantly, these findings are rather independent of small variations of the

V positions, which reflects the strong localization of the V $3d$ states [24]. In addition, the similarity of the bulk and layer partial densities of states builds on the fact that the p - d hybridization resulting from the covalent bonding between V $3d$ and O $2p$ orbitals is similar for both geometries.

In passing, we mention that the Al electronic states resemble those of the bulk aluminate. This is due to the fact that Al_2O_3 is an insulator with a large band gap of about 8.7 eV. For the heterostructure the Al states thus are found far

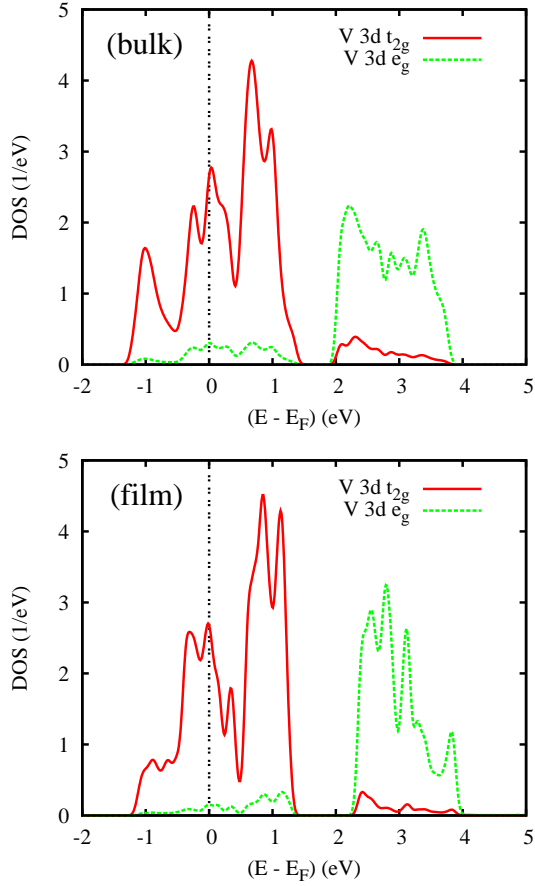


Fig. 2. Partial V $3d$ DOS per atom for the metallic phase of V_2O_3 (upper panel) and for a $\text{V}_2\text{O}_3/\text{Al}_2\text{O}_3$ heterostructure (lower panel). The lower panel, representing the average of all V atoms, indicates a band narrowing which affects the whole V_2O_3 slab. Besides, the data point to only minor alterations of the electronic states in a V_2O_3 thin film because of the contact to an Al_2O_3 substrate.

below and above the Fermi energy, and are hardly influenced by the V states.

The most important difference between the bulk and triple-layer partial densities of states arises from the slightly reduced bandwidths of the latter, again for both the t_{2g} and e_g bands. A similar band narrowing has been observed for the t_{2g} bands of Cr-doped bulk V_2O_3 , where it traces back to a reduction of the $d-d$ overlap coming along with the antidimerization of the V–V pairs parallel to the hexagonal c -axis. In that case, LDA+DMFT calculations have clearly demonstrated that the band narrowing, as induced by the structural changes, drives the metal-insulator transition as soon as the strong electronic correlations, which are only rudimentary covered by the LDA, are properly included [22,23]. Transferring that result to the present situation, we may likewise expect insulating behavior from the reduced bandwidth of triple-layer V_2O_3 .

This finding should be related to the fact that the a lattice constant used here is by 3.5% smaller than that of bulk metallic V_2O_3 and, hence, would be rather in favor of metallic behavior. In addition, the c lattice constant and the fractional coordinates of the atoms in the slab are identical to those of bulk metallic V_2O_3 , which again would preferably lead to metallic behavior. As a consequence, from purely geometric considerations we would expect a broadening of the t_{2g} bands as compared to bulk metallic V_2O_3 , which would be in favor of metallicity even in the presence of strong electronic correlations.

Yet, the opposite situation occurs. From this we conclude that the band narrowing in the triple-layer is mainly caused by the reduced $d-d$ overlap due to the restricted layer-geometry and only to a lesser degree by lattice parameters and atomic parameters. In fact, variation of the a lattice constant (within a reasonable range) has virtually no effect on the magnitude of the band nar-

rowing. As a consequence, taking into account the effect of strong electronic correlations we would expect insulating behavior for rather thin films and a tendency towards metallicity for thicker films. Indeed, this trend has been observed in the experiments [4,5,6,25].

4 Conclusion

In conclusion, electronic structure calculations for a V_2O_3/Al_2O_3 heterostructure point to rather localized $V 3d t_{2g}$ states as compared to the situation in bulk metallic V_2O_3 . Although the interface hardly affects the V_2O_3 electronic states, reduction of the t_{2g} band width due to reduced $d-d$ overlap perpendicular to the layers may cause an insulating ground state of the system if the strong electronic correlations are taken into account. While this mechanism applies mainly to thin films with a thickness of a few V_2O_3 unit cells, increase of the film thickness will more likely drive an insulator-to-metal transition.

Acknowledgments

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